

**Appl. No. 10/655,321
Amdt. dated October 20, 2004
Reply to Office action of July 22, 2004**

Amendments to the Specification:

Please replace paragraph [0001] with the following amended paragraph:

[0001] This application is a continuation of U.S. Application Serial No. 10/036,889, now U.S. Patent No. 6,671,652, filed December 26, 2001, and entitled "Clock Skew Measurement Circuit on a Microprocessor Die."

Please replace paragraph [0011] with the following amended paragraph:

[0011] Two prior art techniques exist for measuring particular signals on a microprocessor die, including clock signals. Both methods involve machining through the bottom of the microprocessor silicon substrate to measure particular signals by observing their affect on hardware of the microprocessor. The first technique involves shining an and-infra-red (IR) lazer at the channel-drain region of metal oxide semiconductor (MOS) transistors in the signal chain of interest. This technique relies on the fact that the IR reflectivity caused by field and carrier effects in the PN junction between the drain and inversion layer change as the particular transistor switches on and off. Data gathering in this first technique must take place over several minutes. The second prior art approach gathers photons emitted from switching transistors. However, a transistor does not release a photon every time it operates, thus requiring the measurement procedure to extend over several hours.